

AMENDMENTS TO THE CLAIMS:

Please cancel claims 16-25 without prejudice or disclaimer of the subject matter thereof.

This listing of claims will replace all prior versions and listings of claims in the above-referenced application.

Listing of Claims:

Claims 1 - 13 (Cancelled)

14. (Previously Presented) An electrostatic discharge device comprising:

- a semiconductor substrate of a first conduction type;

- first and second wells of a second conduction type opposite to said first conduction type, each of said first and second wells including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said second diffusion region in said first well being connected to said first diffusion region in said second well; and

- a third well of said first conduction type located between said first well and said second well, wherein said first, second and third wells cooperate with one another to perform a bipolar action;

- a fourth well of said second conduction type including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said first diffusion region in said fourth well being connected to said second diffusion region in said second well; and

- a fifth well of said first conduction type located between said second well and said fourth well, wherein a voltage applied to said first diffusion region of said first well is higher than a voltage applied to said second diffusion region of said fourth well, and wherein said fifth well is free from a diffusion region of said first conductive type therein.

15. (Previously Presented) The electrostatic discharge device according to claim 14, wherein said second, fourth and fifth well cooperate with one another to perform a bipolar action.

16. - 25. (Cancelled)

26. (Previously Presented) An electrostatic discharge device, comprising:

a semiconductor substrate of a first conduction type;

first and second wells of a second conduction type opposite to said first conduction type, each of said first and second wells including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said second diffusion region in said first well being connected to said first diffusion region in said second well; and

a third well of said first conduction type formed between said first well and said second well and including a diffusion region of said first conduction type, wherein said diffusion region in said third well is divided into a plurality of portions, each of said portions being apart from each other.

27. (Previously Presented) The electrostatic discharge device according to claim 26, wherein said diffusion region in said third well is exposed in a surface of said semiconductor substrate.

28. (Previously Presented) The electrostatic discharge device according to claim 26, wherein said first, second and third wells cooperate with one another to perform a bipolar action.

29. (Previously Presented) The electrostatic discharge device according to claim 26, further comprising:

a fourth well of said second conduction type including a first diffusion region of said first conduction type and a second diffusion region of said second conduction type, said first diffusion region in said fourth well being connected to said second diffusion region in said second well; and

a fifth well of said first conduction type located between said second well and said fourth well, wherein a voltage applied to said first diffusion region of said first well is higher than a voltage applied to said second diffusion region of said fourth well, and wherein said fifth well is free from a diffusion region of said first conductive type therein.

30. (Previously Presented) The electrostatic discharge device according to claim 29, wherein said second, fourth and fifth well cooperate with one another to perform a bipolar action.

31. (Previously Presented) The electrostatic discharge device according to claim 26, wherein said first and second wells are separated from said third well by shallow trench isolation.